

## DESCRIPTION

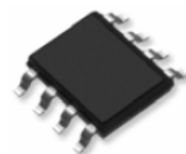
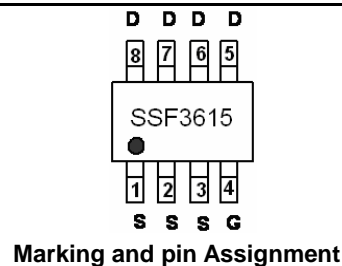
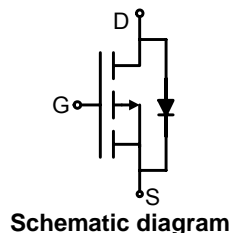
The SSF3615 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

## GENERAL FEATURES

- $V_{DS} = -30V, I_D = -10A$   
 $R_{DS(ON)} < 19m\Omega @ V_{GS} = -4.5V$   
 $R_{DS(ON)} < 11m\Omega @ V_{GS} = -10V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

## Application

- PWM applications
- Load switch
- Power management



SOP-8 top view

## PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
SSF3615	SSF3615	SOP-8	Ø330mm	12mm	3000 units

## ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±25	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D$	-10	A
	$I_{DM}$	-80	A
Maximum Power Dissipation	$P_D$	3.1	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$			-1	μA

Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±25V,V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1.7	-2.3	-3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-7.5A		14	19	mΩ
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A		9	11	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V,I <sub>D</sub> =-10A		18		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V, F=1.0MHz		1200		PF
Output Capacitance	C <sub>OSS</sub>			240		PF
Reverse Transfer Capacitance	C <sub>RSS</sub>			150		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-10V,R <sub>GEN</sub> =3Ω I <sub>D</sub> =1A		9		nS
Turn-on Rise Time	t <sub>r</sub>			8.5		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			20		nS
Turn-Off Fall Time	t <sub>f</sub>			8		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-10A,V <sub>GS</sub> =-10V		18		nC
Gate-Source Charge	Q <sub>gs</sub>			5		nC
Gate-Drain Charge	Q <sub>gd</sub>			3.5		nC
Body Diode Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> =-10A, dI/dt=100A/μs		24		nS
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1A		-0.74	-1	V

## NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

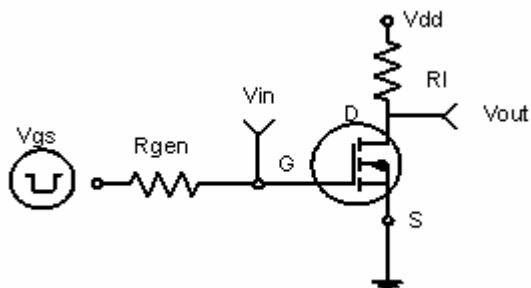


Figure 1: Switching Test Circuit

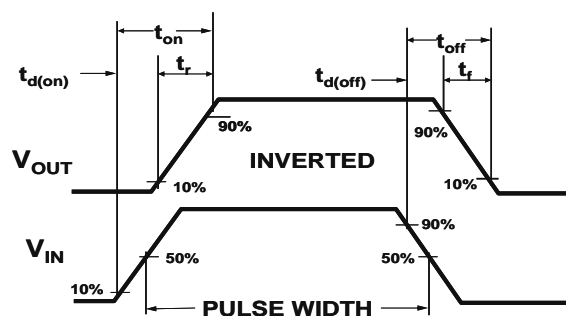


Figure 2: Switching Waveforms

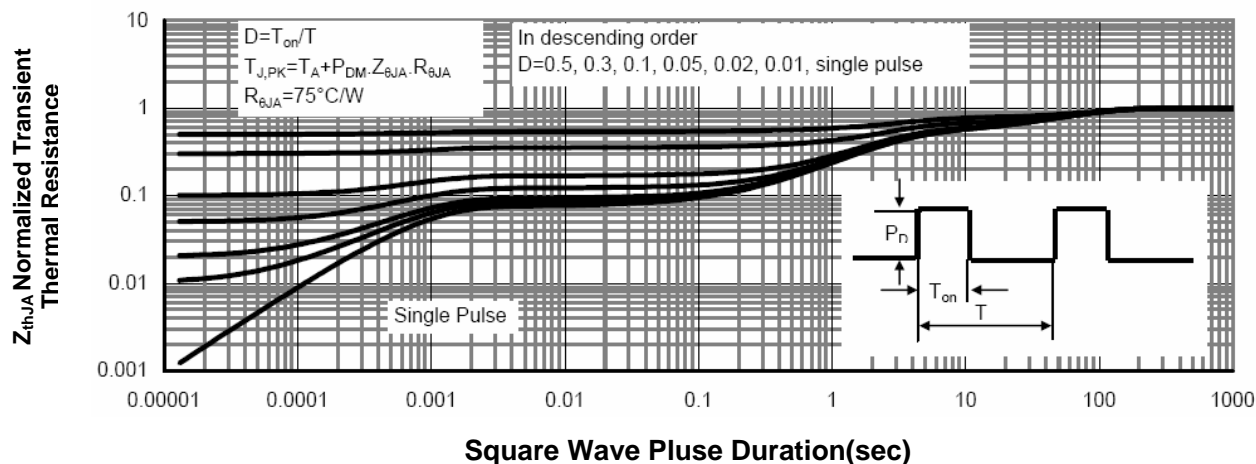
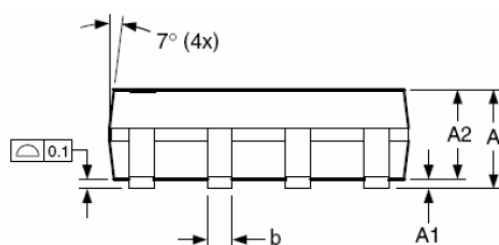
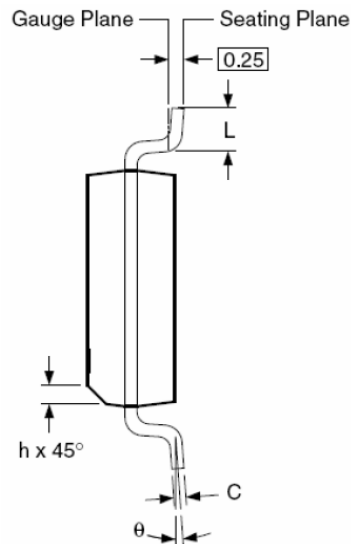
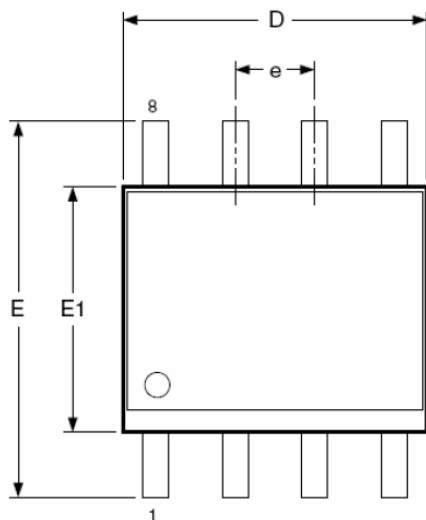
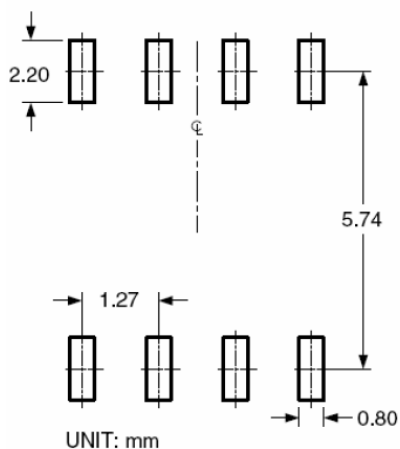


Figure 3: Normalized Maximum Transient Thermal Impedance

## SOP-8 PACKAGE INFORMATION



### RECOMMENDED LAND PATTERN



### Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	1.35	1.65	1.75
A1	0.10	—	0.25
A2	1.25	1.50	1.65
b	0.31	—	0.51
c	0.17	—	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
e	1.27 BSC		
E	5.80	6.00	6.20
h	0.25	—	0.50
L	0.40	—	1.27
θ	0°	—	8°

### Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.053	0.065	0.069
A1	0.004	—	0.010
A2	0.049	0.059	0.065
b	0.012	—	0.020
c	0.007	—	0.010
D	0.189	0.193	0.197
E1	0.150	0.154	0.157
e	0.050 BSC		
E	0.228	0.236	0.244
h	0.010	—	0.020
L	0.016	—	0.050
θ	0°	—	8°

### NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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